

2MBI1000VXB-170E-54

IGBT Modules

IGBT MODULE (V series) 1700V / 1000A / 2 in one package

■ Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



Maximum Ratings and Characteristics

Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions		Maximum ratings	Units	
Collector-Emitter voltage	Vces			1700	V	
Gate-Emitter voltage	V _{GES}			±20	V	
	Ic	Continuous	Tc=25°C	1400		
Ť		Continuous	Tc=100°C	1000		
Section Collector Current	I _{c pulse}	1ms		2000	Α	
드	-lc					
	-I _{c pulse}	1ms		2000		
Collector power dissipation	Pc	1 device		6250	W	
Junction temperature	T _j			175		
Operating junction temperature (under switching conditions)	T _{jop}			150	°C	
Case temperature	Tc			150	C	
Storage temperature	T _{stg}			-40 ~ +150		
Isolation voltage between terminal and copper base (*1)	V _{iso}	AC : 1min.		4000	VAC	
between thermistor and others (*2)	Viso	AC . IIIIII.		4000	VAC	
Mounting		M5		6.0		
Screw torque (*3) Main Terminals]-	M8		10.0	N m	
Sense Terminals		M4		2.1		

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable Value: Mounting 3.0 ~ 6.0 Nm (M5) Recommendable Value: Main Terminals 8.0 ~ 10.0 Nm (M8)

Recommendable Value: Sense Terminals 1.8 ~ 2.1 Nm (M4)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items		Cumbala	Conditions		Ch	aracterist	ics	Units
		Symbols	Conditions	min.	typ.	max.	Units	
	Zero gate voltage collector current	Ices	$V_{GE} = 0V, V_{CE} = 1700V$		-	-	6.0	mA
	Gate-Emitter leakage current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	1200	nA
	Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 1000mA		6.0	6.5	7.0	V
		V _{CE (sat)}		T _j =25°C	-	2.10	2.55	
		(terminal)		T _j =125°C	-	2.50	-	
	Callastan Emittan actionation valtage	(*4)	V _{GE} = 15V	T _j =150°C	-	2.55	-	V
	Collector-Emitter saturation voltage	.,	Ic = 1000A	T _j =25°C	-	2.00	2.45	
		V _{CE} (sat)		T _j =125°C	-	2.40	-	
		(chip)		T _j =150°C	-	2.45	-	
	Input capacitance	Rg _(int)	-		-	1.17	-	Ω
ē		Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1N	1Hz	-	94	-	nF
nverte		ton	V _{cc} = 900V		-	1250	-	
2	Turn-on time	t	Ic = 1000A		-	500	-	
_		t _{r (i)}	$V_{GE} = \pm 15V$ $R_{G} = +1.2/-1.8\Omega$ $L_{S} = 60 nH$		-	150	-	nsec
	T (C.)	toff			-	1550	-	
	Turn-off time	tr			-	150	-	
		VF		T _i =25°C	-	1.95	2.40	
	Forward on voltage (tel (*4) V _F	(terminal)		T _i =125°C	-	2.20	-	
		(*4)	$V_{GE} = 0V$	T _i =150°C	-	2.15	-	.,
		.,	I _F = 1000A	T _i =25°C	-	1.85	2.30	V
				T _i =125°C	-	2.10	-	
		(chip)		T=150°C -	-	2.05	-	1
	Reverse recovery time	t _{rr}	I _F = 1000A		-	240	-	nsec
ģ	D	Б	T=25°C		- 5000 -		-	Ω
Thermistor	Resistance	R	T=100°C		465	495	520	
를	B value	В	T=25/50°C	,	3305	3375	3450	К

Note $^{\star}1$: Please refer to page 7 , there is definition of on-state voltage at terminal.

● Thermal resistance characteristics

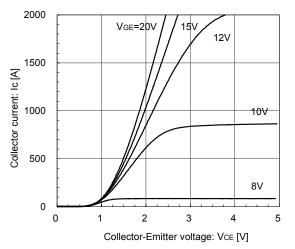
Items	Symbols	Conditions	Characteristics		Units	
	Symbols	Conditions	min.	typ.	max.	Ullits
Thermal resistance (1device)	Dth/i o)	Inverter IGBT	-	-	0.024	
	Rth(j-c)	Inverter FWD	-	-	0.048	°C/W
Contact thermal resistance (1device) (*5)	Rth(c-f)	with Thermal Compound	•	0.0083	-	

Note \star 5: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

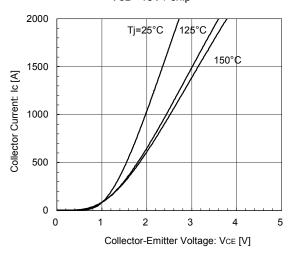
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Tj= 25° C / chip



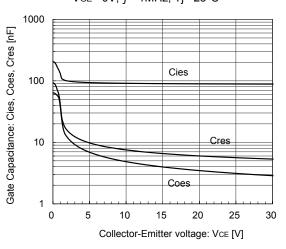
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) VGE= 15V / chip



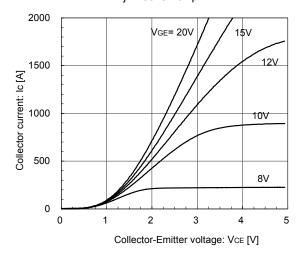
[INVERTER]

Gate Capacitance vs. Collector-Emitter Voltage (typ.) VgE= 0V, f= 1MHz, Tj= 25°C



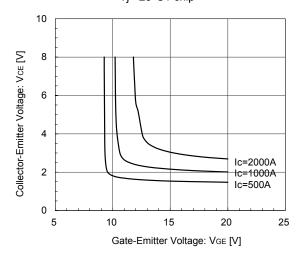
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Tj= 150°C / chip



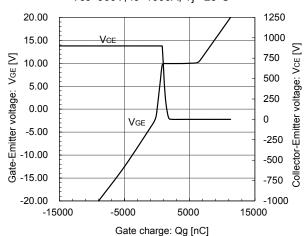
[INVERTER]

Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) Tj= 25°C / chip



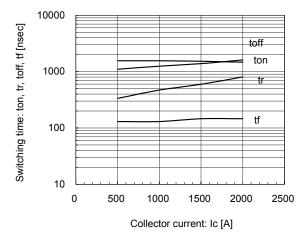
[INVERTER]
Dynamic Gate Charge (typ.)

Vcc=900V, Ic=1000A, Tj= 25°C



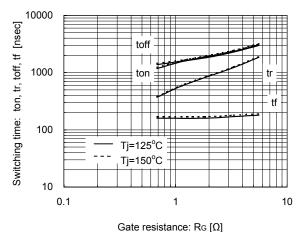
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=900V, $VgE=\pm15V$, $Rg=+1.2/-1.8\Omega$, $Tj=25^{\circ}C$



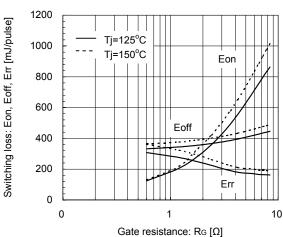
[INVERTER]

Switching time vs. Gate resistance (typ.) Vcc=900V, Ic=1000A, VgE=±15V, Tj=125°C, 150°C



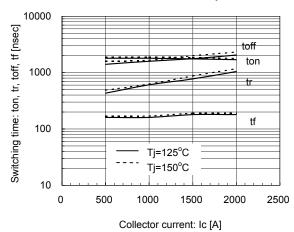
[INVERTER]

Switching loss vs. Gate resistance (typ.) Vcc=900V, Ic=1000A, VgE=±15V, Tj=125°C, 150°C



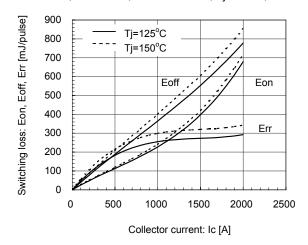
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=900V, VgE= \pm 15V, Rg= \pm 1.2/-1.8 Ω , Tj=125°C, 150°C



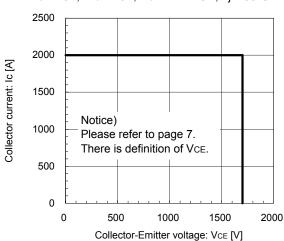
[INVERTER]

Switching loss vs. Collector current (typ.) Vcc=900V, VgE= \pm 15V, Rg= \pm 1.2/-1.8 Ω , Tj=125°C, 150°C



[INVERTER]

Reverse bias safe operating area (max.) +VgE=15V, -VgE=15V, Rg=+1.2/-1.8 Ω , Tj=150°C



0

0

Forward Current vs. Forward Voltage (typ.) chip

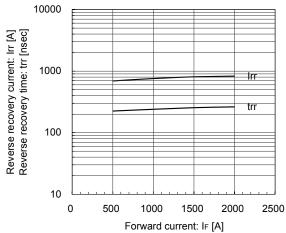
2000

Tj=25°C

1500

Tj=25°C

[INVERTER]
Reverse Recovery Characteristics (typ.)
Vcc=900V, VgE=±15V, Rg=+1.2/-1.8Ω, Tj=25°C

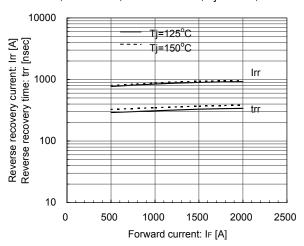


[INVERTER]
Reverse Recovery Characteristics (typ.)
Vcc=900V, VgE=±15V, Rg=+1.2/-1.8Ω, Tj=125°C, 150°C

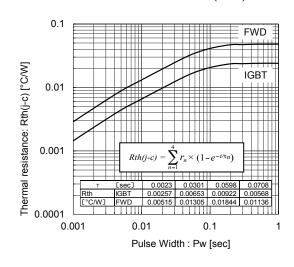
2

Forward on voltage: VF [V]

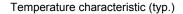
3

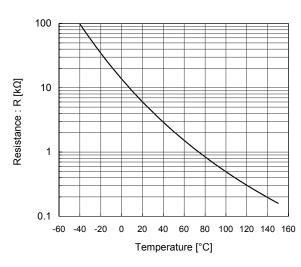


Transient Thermal Resistance (max.)

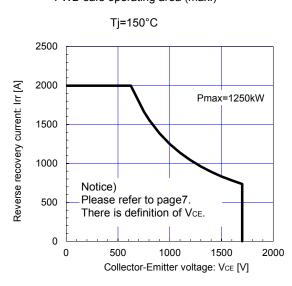


[THERMISTOR]

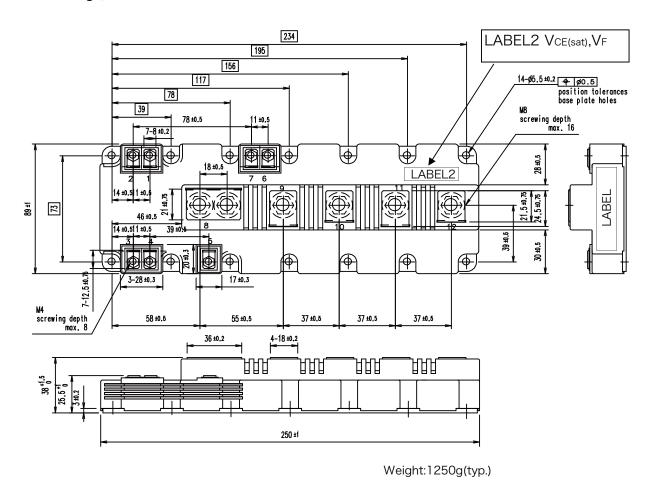




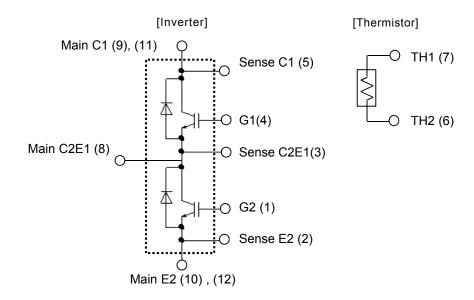
FWD safe operating area (max.)



■ Outline Drawings, mm

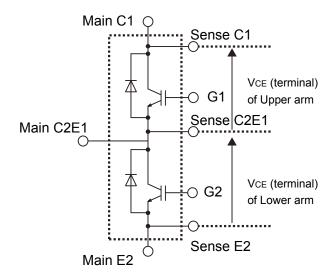


■ Equivalent Circuit Schematic



http://www.fujielectric.com/products/semiconductor/

■ Definition of on-state voltage at terminal and switching characteristics



Fuji defined VcE value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm.

Switching characteristics of VcE also is defined between Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Please use these terminals whenever measure spike voltage and on-state voltage .

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